

# N-Channel 80 V (D-S) Power MOSFET

| Р | PRODUCT SUMMARY     |                               |                                 |                       |  |  |  |  |  |
|---|---------------------|-------------------------------|---------------------------------|-----------------------|--|--|--|--|--|
| \ | / <sub>DS</sub> (V) | $R_{DS(on)}(m\Omega)(Typ.)$   | I <sub>D</sub> (A) <sup>a</sup> | Q <sub>g</sub> (Typ.) |  |  |  |  |  |
|   | 80                  | 8.5 at V <sub>GS</sub> = 10 V | 45                              | 18.3 nC               |  |  |  |  |  |

#### **FEATURES**

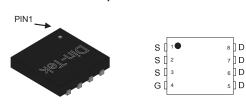
- DT-Trench Power MOSFET
- 100 % Rg and UIS Tested
- · RoHS Compliant

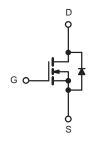
#### **APPLICATIONS**

- · Notebook PC Core
- VRM/POL

#### PDFN3.3X3.3-8L Pin Configuration

**Top View** 





N-Channel MOSFET

| ABSOLUTE MAXIMUM RATINGS   | $(T_C = 25  ^{\circ}C, \text{ unless other})$ | wise noted)                       |             |      |  |
|--|---|-----------------------------------|-------------|------|--|
| PARAMETER  |   |                                   | LIMIT       | UNIT |  |
| Drain-Source Voltage   | V <sub>DS</sub>                               | 80                                |             |      |  |
| Gate-Source Voltage  | V <sub>GS</sub>                               | ± 20                              | V           |      |  |
| Continuous Drain Current (T <sub>.I</sub> = 150 °C) <sup>a</sup> | T <sub>C</sub> = 25 °C                        | 1                                 | 45          | A    |  |
| Continuous Diam Current (1) = 150 °C)                            | T <sub>C</sub> = 100 °C                       | - I <sub>D</sub>                  | 33          |      |  |
| Pulsed Drain Current <sup>b</sup>                                | I <sub>DM</sub>                               | 180                               | A           |      |  |
| Single Pulse Avalanche Current                                   | IAS   | 28                                |             |      |  |
| Single Avalanche Energy  | E <sub>AS</sub>                               | 189                               | mJ          |      |  |
| Maximum Power Discipations                                       | T <sub>C</sub> = 25 °C                        | В                                 | 43          | W    |  |
| Maximum Power Dissipation <sup>c</sup>                           | T <sub>C</sub> = 100 °C                       | P <sub>D</sub>                    | 17.2        | VV   |  |
| Operating Junction and Storage Temperature Range                 |   | T <sub>J</sub> , T <sub>stg</sub> | -55 to +150 | °C   |  |

| THERMAL RESISTANCE RATINGS                   |  |       |      |  |  |
|--|--|-------|------|--|--|
| PARAMETER                                    | SYMBOL   | LIMIT | UNIT |  |  |
| Junction-to-Ambient (PCB Mount) <sup>d</sup> | ient (PCB Mount) <sup>d</sup> R <sub>thJA</sub> 55 |       |      |  |  |
| Junction-to-Case (Drain)                     | R <sub>thJC</sub>                                  | 2.9   | °C/W |  |  |

#### Notes

- a. Calculated continuous current based on maximum allowablejunction temperature.
- b. Repetitive rating; pulse width limited by max. junction temperature.
- c. Pd is based on max. junction temperature, using junction-case thermal resistance.
- d. The value of R<sub>0JA</sub> is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper,in a still air environment with Ta=25 °C.



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| PARAMETER                                     | SYMBOL              | TEST CONDITIONS  | MIN. | TYP. | MAX.  | UNIT |  |
|---|---------------------|--|------|------|-------|------|--|
| Static  |                     |  |      |      |       |      |  |
| Drain-Source Breakdown Voltage V <sub>I</sub> |                     | V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA                     | 80   | -    | -     | V    |  |
| Gate Threshold Voltage                        | V <sub>GS(th)</sub> | $V_{DS} = V_{GS}, I_D = 250 \mu A$                                 | 2    | -    | 3     | V    |  |
| Gate-Body Leakage                             | I <sub>GSS</sub>    | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$                  | -    | -    | ± 100 | nA   |  |
| Zoro Coto Voltago Drain Current               | I <sub>DSS</sub>    | $V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$                      | -    | -    | 1     | μА   |  |
| Zero Gate Voltage Drain Current               |                     | VDS = 64 V, VGS = 0 V, TJ = 55 °C                                  | -    | -    | 10    |      |  |
| On-State Drain Current <sup>a</sup>           | I <sub>D(on)</sub>  | $V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$                    | 45   | -    | -     | Α    |  |
| Drain-Source On-State Resistance <sup>a</sup> | R <sub>DS(on)</sub> | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A                      | -    | 8.5  | 10.5  | mΩ   |  |
| Forward Transconductance <sup>a</sup>         | 9 <sub>fs</sub>     | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 20 A                      | -    | 34   | -     | S    |  |
| Dynamic <sup>b</sup>                          |                     |  |      |      |       |      |  |
| Input Capacitance                             | C <sub>iss</sub>    |  | -    | 1150 | -     | pF   |  |
| Output Capacitance                            | C <sub>oss</sub>    | V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 40 V, f = 1 MHz           | -    | 635  | -     |      |  |
| Reverse Transfer Capacitance                  | C <sub>rss</sub>    | İ  | -    | 9.8  | -     |      |  |
| Total Gate Charge <sup>c</sup>                | $Q_g$               |  | -    | 18.3 | -     | nC   |  |
| Gate-Source Charge <sup>c</sup>               | Q <sub>gs</sub>     | $V_{DS} = 40 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$ | -    | 3.9  | -     |      |  |
| Gate-Drain Charge <sup>c</sup>                | $Q_{gd}$            | İ  | -    | 4.5  | -     |      |  |
| Gate Resistance                               | $R_g$               | f = 1 MHz  |      | 2.1  | -     | Ω    |  |
| Turn-On Delay Time <sup>c</sup>               | t <sub>d(on)</sub>  |  | -    | 12.2 | -     |      |  |
| Rise Time <sup>c</sup>                        | t <sub>r</sub>      | $V_{DS} = 40 \text{ V}, R_{GEN} = 5 \Omega, V_{GS} = 10 \text{ V}$ | -    | 6.3  | -     | ns   |  |
| Turn-Off Delay Time <sup>c</sup>              | t <sub>d(off)</sub> | I <sub>D</sub> = 10 A  | -    | 21   | -     |      |  |
| Fall Time <sup>c</sup>                        | t <sub>f</sub>      | İ  | -    | 9.4  | -     |      |  |
| <b>Drain-Source Body Diode Ratings and</b>    | Characterist        | ics <sup>b</sup> (T <sub>J</sub> = 25 °C)                          |      |      |       |      |  |
| Continuous Source-Drain Diode Current         | I <sub>S</sub>      | T <sub>C</sub> = 25 °C   | -    | -    | 45    | Α    |  |
| Pulsed Current                                | I <sub>SM</sub>     |  | -    | -    | 180   | Α    |  |
| Forward Voltage <sup>a</sup>                  | $V_{SD}$            | I <sub>F</sub> = 1 A , V <sub>GS</sub> = 0 V                       | -    | 0.6  | -     | V    |  |
| Reverse Recovery Time                         | t <sub>rr</sub>     |  | -    | 28   | -     | ns   |  |
| Reverse Recovery Charge                       | Q <sub>rr</sub>     | I <sub>F</sub> = 20 A, di/dt = 100 A/μs                            | -    | 127  | -     | nC   |  |

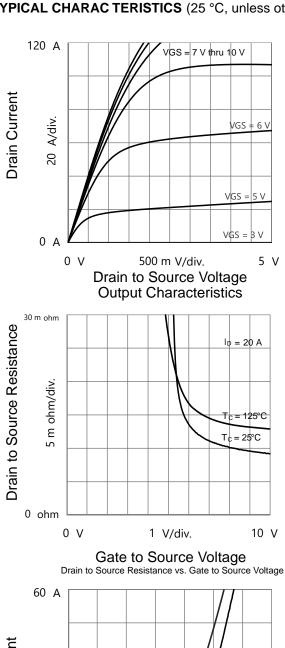
#### Notes

- a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those in dicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



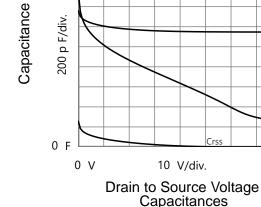
### TYPICAL CHARAC TERISTICS (25 °C, unless otherwise noted)



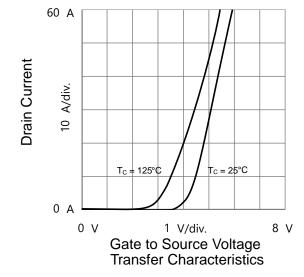
Source Current 10 A/div.  $T_C \neq 25^{\circ}C$  $T_C = 125^{\circ}C$ 0 A 0 V 200 m V/div. 1.4 V

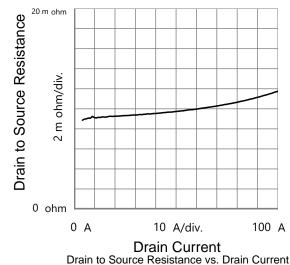
Source to Drain Voltage

**Body Diode Forward Characteristics** 



2 n F

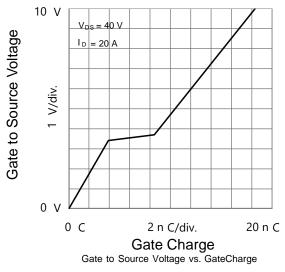


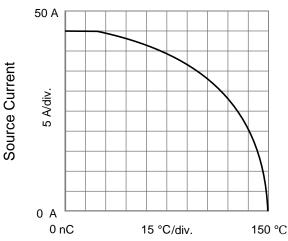


80 V

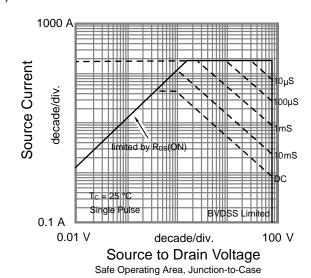


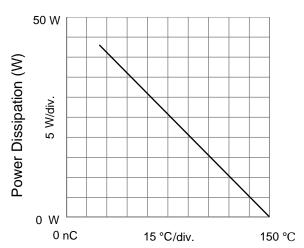
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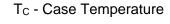


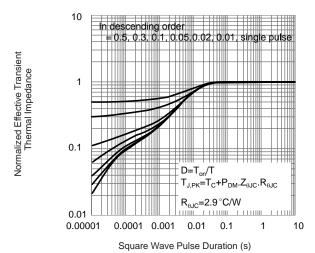


T<sub>C</sub> - Case Temperature





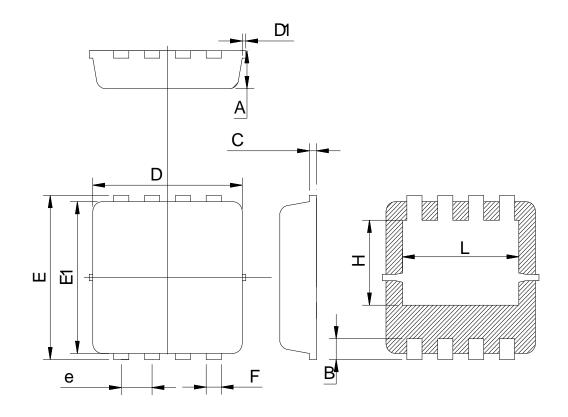




Normalized Thermal Transient Impedance, Junction-to-Case



# PDFN 3.3X3.3-8L PACKAGE OUTLINE



## **COMMON DIMENSIONS** (UNITS OF MEASURE=MILLIMETER)

| Symbol | Min   | Тур   | Max   |
|--------|-------|-------|-------|
| Α      | 0.600 | 0.775 | 1.000 |
| В      | 0.20  | 0.38  | 0.55  |
| С      | 0.05  | 0.15  | 0.40  |
| D      | 3.10  | 3.25  | 3.50  |
| D1     | -     | -     | 0.15  |
| Е      | 3.15  | 3.35  | 3.50  |
| E1     | 2.60  | 3.10  | 3.45  |
| е      | 0.50  | 0.65  | 0.80  |
| F      | 0.15  | 0.32  | 0.45  |
| Н      | 1.25  | 1.73  | 2.10  |
| L      | 2.20  | 2.45  | 2.85  |





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